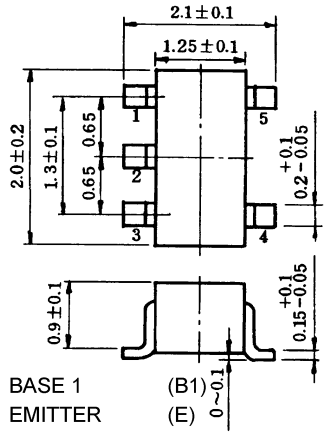
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1873

Audio Frequency General Purpose Amplifier Applications

- Small package (dual type)
- High voltage and high current: V_{CEO} = −50 V, I_C = −150 mA (max)
- High h_{FE}
- Excellent h_{FE} linearity: h_{FE} (I_C = −0.1 mA)/h_{FE} (I_C = −2 mA) = 0.95 (typ.)
- Complementary to 2SC4944

Unit: mm



1. BASE 1 (B1)
2. EMITTER (E)
3. BASE 2 (B2)
4. COLLECTOR 2 (C2)
5. COLLECTOR 1 (C1)

USV

JEDEC	—
JEITA	—
TOSHIBA	2-2L1A

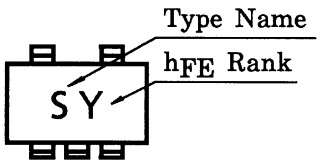
Weight: 6.2 mg (typ.)

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

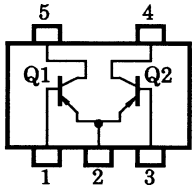
Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−50	V
Collector-emitter voltage	V_{CEO}	−50	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−150	mA
Base current	I_B	−30	mA
Collector power dissipation	P_C (Note)	200	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

Note 1: Total rating

Marking



Equivalent Circuit (top view)



Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

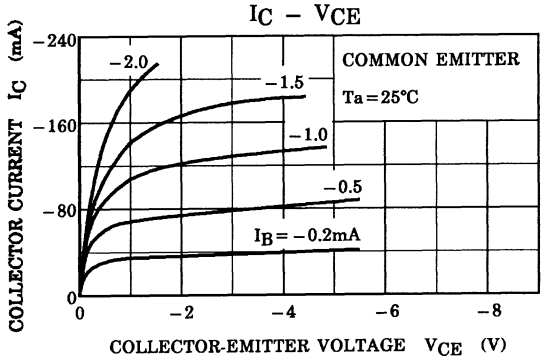
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −50 V, I_E = 0	—	—	−0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−0.1	μA
DC current gain	h_{FE} (Note)	V_{CE} = −6 V, I_C = −2 mA	120	—	400	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = −100 mA, I_B = −10 mA	—	−0.1	−0.3	V
Transition frequency	f_T	V_{CE} = −10 V, I_C = −1 mA	80	—	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	4	7	pF

Note 2: h_{FE} classification Y (Y): 120~240, GR (G): 200~400

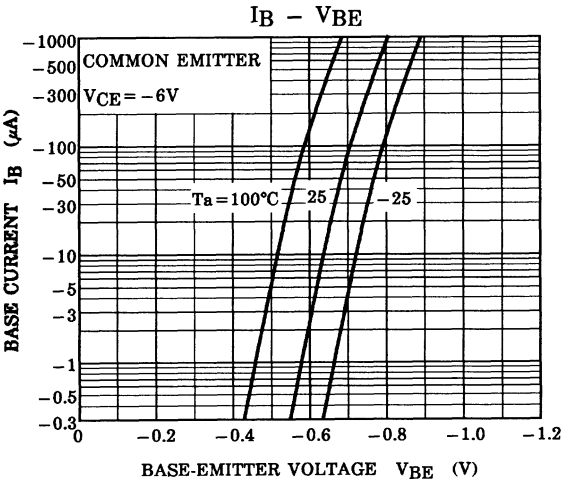
( ) marking symbol

(Q1, Q2 common)

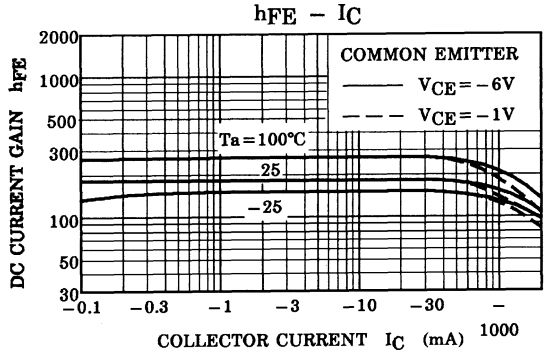
$I_C - V_{CE}$



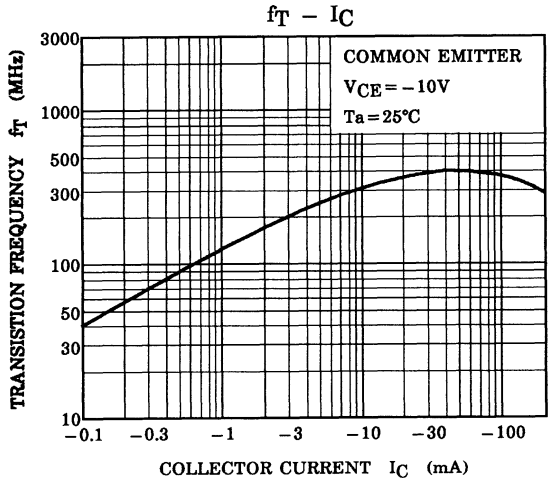
$I_B - V_{BE}$



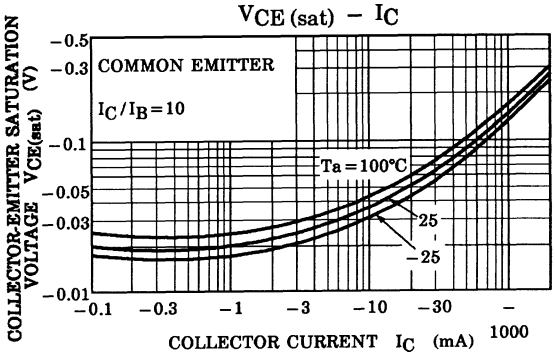
$h_{FE} - I_C$



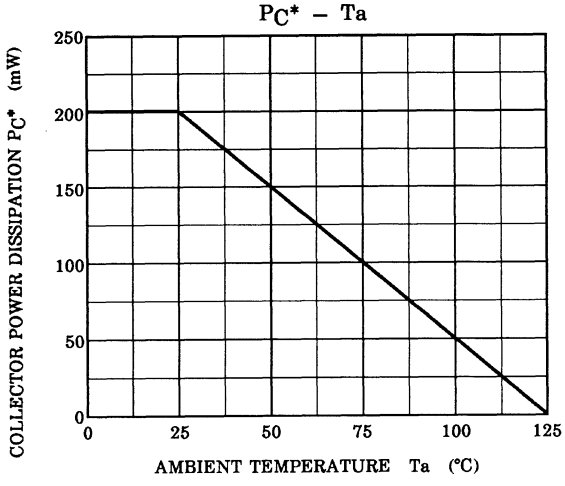
$f_T - I_C$



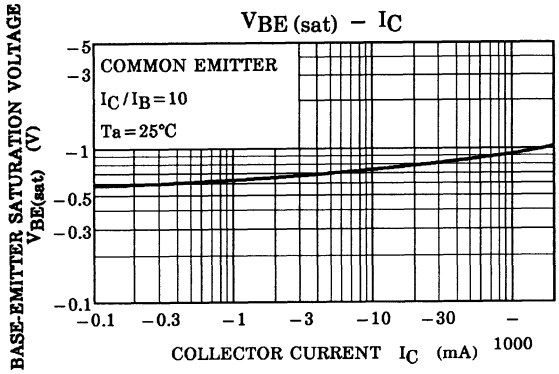
$V_{CE\,(sat)} - I_C$



$P_C^* - Ta$



$V_{BE\,(sat)} - I_C$



*: Total rating

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